

II. AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior versions, and listings, of claims in the application:

1-7. (Cancelled)

8. (Currently Amended) A transistor comprising:

a remaining portion of an emitter landing pad that is distanced from an intrinsic base, wherein the remaining portion is distanced from the intrinsic base by an extrinsic base layer, and the extrinsic base layer includes an oxide section that determines a distance between an emitter and an extrinsic base, wherein a width of the oxide section determines a base resistance.

9. (Cancelled)

10. (Cancelled)

11. (Currently Amended) The transistor of claim 10 8, wherein the width of the oxide section determines a length of the remaining portion that current must traverse as current passes through the extrinsic base.

12. (Original) The transistor of claim 11, wherein the thickness of the oxide section is sufficient to prevent current from having to traverse the remaining portion.

13. (Original) A transistor comprising:
- an emitter;
 - a first extrinsic base layer;
 - a second extrinsic base layer electrically connected to the first extrinsic base layer;
 - an oxide section in the first extrinsic base layer adjacent the emitter; and
 - a remaining portion of an emitter landing pad that separates each of the first and second extrinsic base layer from one another adjacent the emitter.
14. (Original) The transistor of claim 13, wherein the extrinsic base includes the first extrinsic base layer and a second extrinsic base layer, and the first extrinsic base layer is doped at a different concentration than the second extrinsic base layer.
15. (Original) The transistor of claim 14, wherein the oxide section is positioned within the first extrinsic base layer.
16. (Original) The transistor of claim 14, wherein the first extrinsic base layer includes a first region including a doped silicon and a second region includes a doped polysilicon, and the oxide section is in the first region.
17. (Original) The transistor of claim 13, further comprising a remaining portion of an emitter landing pad positioned above the oxide section.

18. (Original) The transistor of claim 13, wherein a width of the oxide section determines a base resistance.
19. (Original) The transistor of claim 18, wherein the width of the oxide section determines a length of the remaining portion that current must traverse as the current passes through the extrinsic base.
20. (Original) The transistor of claim 19, wherein the thickness of the oxide section is sufficient to prevent the current from having to traverse the remaining portion.
21. (Original) The transistor of claim 13, wherein the emitter extends under a portion of a spacer.
22. (Original) The transistor of claim 13, wherein the first and second extrinsic base layers extend in a horizontally overlapped fashion from the emitter to a common edge.
23. (Original) A transistor comprising:
an emitter extending through a remaining portion of an emitter landing pad to an intrinsic base; and
an oxide section in an extrinsic base layer, the oxide portion extending below a part of the remaining portion,
wherein a width of the oxide section determines an amount of base resistance.

24. (Original) The transistor of claim 23, wherein the thickness determines a length of the remaining portion that current must traverse as the current passes through an extrinsic base.

25. (Original) The transistor of claim 23, wherein the extrinsic base layer extends under another part of the remaining portion and elevates the remaining portion from the intrinsic base.

26. (Original) The transistor of claim 25, wherein the extrinsic base includes a first layer and a second layer, and the oxide section is positioned within the first layer, and the first layer includes a first region including a doped silicon and a second region including a doped polysilicon.

27-30. (Cancelled)